Seung Hwan Lee

List of Publications by Year in descending order

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17 papers	1,708 citations	932766 10 h-index	1199166 12 g-index
18	18	18	1762
all docs	docs citations	times ranked	citing authors

#	Article	IF	CITATIONS
1	Reservoir computing using dynamic memristors for temporal information processing. Nature Communications, 2017, 8, 2204.	5.8	547
2	A fully integrated reprogrammable memristor–CMOS system for efficient multiply–accumulate operations. Nature Electronics, 2019, 2, 290-299.	13.1	469
3	Temporal data classification and forecasting using a memristor-based reservoir computing system. Nature Electronics, 2019, 2, 480-487.	13.1	309
4	Nanoscale resistive switching devices for memory and computing applications. Nano Research, 2020, 13, 1228-1243.	5.8	91
5	A Deep Neural Network Accelerator Based on Tiled RRAM Architecture. , 2019, , .		46
6	Integration of 4F2 selector-less crossbar array 2Mb ReRAM based on transition metal oxides for high density memory applications. , 2012 , , .		41
7	Nanoionic Resistiveâ€Switching Devices. Advanced Electronic Materials, 2019, 5, 1900184.	2.6	41
8	Quantitative, Dynamic TaO _{<i>x</i>} Memristor/Resistive Random Access Memory Model. ACS Applied Electronic Materials, 2020, 2, 701-709.	2.0	38
9	Vertical atomic manipulation with dynamic atomic-force microscopy without tip change via a multi-step mechanism. Nature Communications, 2014, 5, 4476.	5.8	32
10	Memristors Based on (Zr, Hf, Nb, Ta, Mo, W) Highâ€Entropy Oxides. Advanced Electronic Materials, 2021, 7, 2001258.	2.6	22
11	Chemical tip fingerprinting in scanning probe microscopy of an oxidized Cu(110) surface. Physical Review B, 2012, 86, .	1.1	21
12	A Fully Integrated Reprogrammable CMOS-RRAM Compute-in-Memory Coprocessor for Neuromorphic Applications. IEEE Journal on Exploratory Solid-State Computational Devices and Circuits, 2020, 6, 36-44.	1.1	20
13	The Effect of Tunnel Barrier at Resistive Switching Device for Low Power Memory Applications. , 2011, ,		10
14	Vertical double gate Z-RAM technology with remarkable low voltage operation for DRAM application. , 2010, , .		8
15	Image formation and contrast inversion in noncontact atomic force microscopy imaging of oxidized Cu(110) surfaces. Physical Review B, 2014, 90, .	1.1	8
16	Growth models of coexisting (i) p(2 \tilde{A} — 1) and (i) c(6 \tilde{A} — 2) phases on an oxygen-terminated Cu(110) surface studied by noncontact atomic force microscopy at 78 K. Nanotechnology, 2016, 27, 205702.	1.3	2
17	Deep Neural Network Mapping and Performance Analysis on Tiled RRAM Architecture. , 2020, , .		2